

## Standard SCRs, 20A

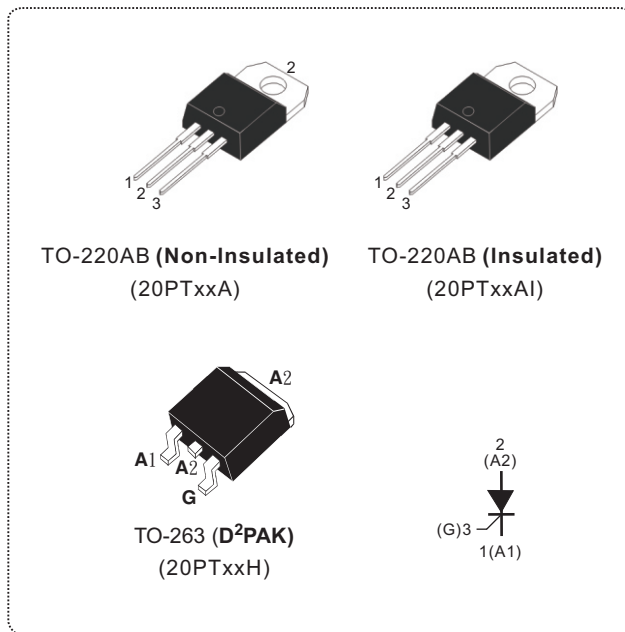
### Main Features

| Symbol            | Value       | Unit |
|-------------------|-------------|------|
| $I_{T(RMS)}$      | 20          | A    |
| $V_{DRM}/V_{RRM}$ | 600 to 1000 | V    |
| $I_{GT}$          | 3 to 25     | mA   |

### DESCRIPTION

The 20PT series of silicon controlled rectifiers are high performance glass passivated technology, and are suitable for general purpose applications.

Using clip assembly technology, they provide a superior performance in surge current capabilities.



### ABSOLUTE MAXIMUM RATINGS

| PARAMETER                                                                                       | SYMBOL       | TEST CONDITIONS           |                           | VALUE         | UNIT                   |
|-------------------------------------------------------------------------------------------------|--------------|---------------------------|---------------------------|---------------|------------------------|
| RMS on-state current full sine wave<br>(180° conduction angle)                                  | $I_{T(RMS)}$ | TO-263/TO-220AB           | $T_c = 100^\circ\text{C}$ | 20            | A                      |
|                                                                                                 |              | TO-220AB insulated        | $T_c = 80^\circ\text{C}$  |               |                        |
| Average on-state current<br>(180° conduction angle)                                             | $I_{T(AV)}$  | TO-263/TO-220AB           | $T_c = 100^\circ\text{C}$ | 13            | A                      |
|                                                                                                 |              | TO-220AB insulated        | $T_c = 80^\circ\text{C}$  |               |                        |
| Non repetitive surge peak on-state current<br>(full cycle, $T_j$ initial = $25^\circ\text{C}$ ) | $I_{TSM}$    | F = 50 Hz                 | t = 20 ms                 | 200           | A                      |
|                                                                                                 |              | F = 60 Hz                 | t = 16.7 ms               | 220           |                        |
| $I^2t$ Value for fusing                                                                         | $I^2t$       | $t_p = 10 \text{ ms}$     |                           | 200           | $\text{A}^2\text{s}$   |
| Critical rate of rise of on-state current<br>$I_G = 2 \times I_{GT}$ , $t_i \leq 100\text{ns}$  | $di/dt$      | F = 60 Hz                 | $T_j = 125^\circ\text{C}$ | 50            | $\text{A}/\mu\text{s}$ |
| Peak gate current                                                                               | $I_{GM}$     | $T_p = 20 \mu\text{s}$    | $T_j = 125^\circ\text{C}$ | 4             | A                      |
| Maximum gate power                                                                              | $P_{GM}$     | $T_p = 20 \mu\text{s}$    | $T_j = 125^\circ\text{C}$ | 10            | W                      |
| Average gate power dissipation                                                                  | $P_{G(AV)}$  | $T_j = 125^\circ\text{C}$ |                           | 1             | W                      |
| Repetitive peak off-state voltage                                                               | $V_{DRM}$    | $T_j = 125^\circ\text{C}$ |                           | 600 to 1000   | V                      |
| Repetitive peak reverse voltage                                                                 | $V_{RRM}$    |                           |                           |               |                        |
| Storage temperature range                                                                       | $T_{stg}$    |                           |                           | - 40 to + 150 | $^\circ\text{C}$       |
| Operating junction temperature range                                                            | $T_j$        |                           |                           | - 40 to + 125 |                        |

| ELECTRICAL SPECIFICATIONS (T <sub>J</sub> = 25 °C unless otherwise specified) |                                                                                               |                        |      |          |      |
|-------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|------------------------|------|----------|------|
| SYMBOL                                                                        | TEST CONDITIONS                                                                               |                        |      | 20PTxxxx | Unit |
| I <sub>GT</sub>                                                               | V <sub>D</sub> = 12V, R <sub>L</sub> = 33Ω                                                    |                        | Min. | 3        | mA   |
|                                                                               |                                                                                               |                        | Max. | 25       |      |
| V <sub>GT</sub>                                                               |                                                                                               |                        | Max. | 1.3      | V    |
| V <sub>GD</sub>                                                               | V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> = 3.3KΩ<br>R <sub>GK</sub> = 220Ω          | T <sub>J</sub> = 125°C | Min. | 0.2      | V    |
| I <sub>H</sub>                                                                | I <sub>T</sub> = 500mA, Gate open                                                             |                        | Max. | 40       | mA   |
| I <sub>L</sub>                                                                | I <sub>G</sub> = 1.2×I <sub>GT</sub>                                                          |                        | Min. | 60       | mA   |
| dV/dt                                                                         | V <sub>D</sub> = 67% V <sub>DRM</sub> , Gate open                                             | T <sub>J</sub> = 125°C | Min. | 500      | V/μs |
| V <sub>TM</sub>                                                               | I <sub>T</sub> = 40A, t <sub>p</sub> = 380μs                                                  | T <sub>J</sub> = 25°C  | Max. | 1.6      | V    |
| I <sub>DRM</sub><br>I <sub>RRM</sub>                                          | V <sub>D</sub> =V <sub>DRM</sub> , V <sub>R</sub> =V <sub>RRM</sub><br>R <sub>GK</sub> = 220Ω | T <sub>J</sub> = 25°C  | Max. | 5        | μA   |
|                                                                               |                                                                                               | T <sub>J</sub> = 125°C | Max. | 2        | mA   |
| V <sub>to</sub>                                                               | Threshold Voltage                                                                             | T <sub>J</sub> = 125°C | Max. | 0.77     | V    |
| R <sub>d</sub>                                                                | Dynamic Resistance                                                                            | T <sub>J</sub> = 125°C | Max. | 23       | mΩ   |

| THERMAL RESISTANCE   |                       |                                                  |       |      |
|----------------------|-----------------------|--------------------------------------------------|-------|------|
| SYMBOL               | Parameter             |                                                  | VALUE | UNIT |
| R <sub>th(j-c)</sub> | Junction to case (DC) | D <sup>2</sup> PAK/TO-220AB                      | 1.05  | °C/W |
|                      |                       | TO-220AB insulated                               | 2.1   |      |
| R <sub>th(j-a)</sub> | Junction to ambient   | S = 1 cm <sup>2</sup> TO-263(D <sup>2</sup> PAK) | 45    | °C/W |
|                      |                       | TO-220AB/TO-220AB insulated                      | 60    |      |

S=Copper surface under tab

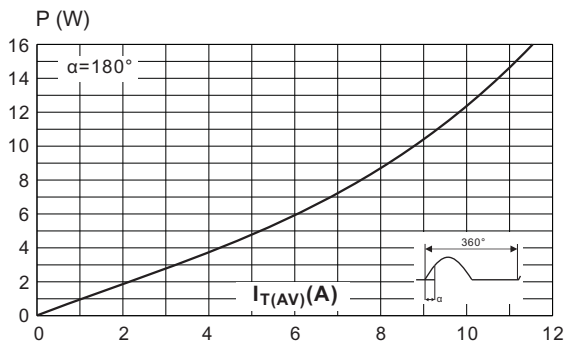
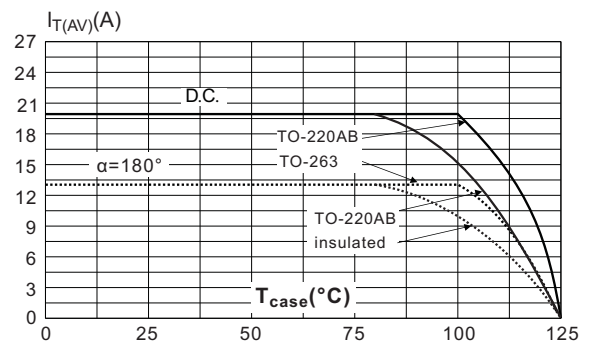
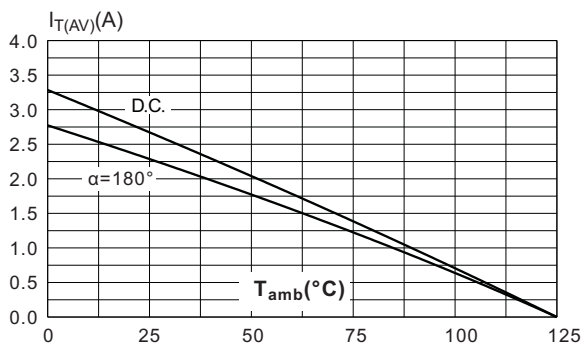
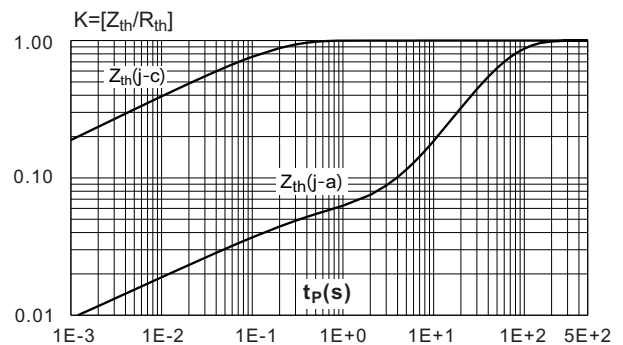
| PRODUCT SELECTOR |              |       |        |             |                    |
|------------------|--------------|-------|--------|-------------|--------------------|
| PART NUMBER      | VOLTAGE (xx) |       |        | SENSITIVITY | PACKAGE            |
|                  | 600 V        | 800 V | 1000 V |             |                    |
| 20PTxxA/20PTxxAI | V            | V     | V      | 25 mA       | TO-220AB           |
| 20PTxxH          | V            | V     | V      | 25 mA       | D <sup>2</sup> PAK |

| ORDERING INFORMATION |          |                            |        |           |               |
|----------------------|----------|----------------------------|--------|-----------|---------------|
| ORDERING TYPE        | MARKING  | PACKAGE                    | WEIGHT | BASE Q'TY | DELIVERY MODE |
| 20PTxxA              | 20PTxxA  | TO-220AB                   | 2.0g   | 50        | Tube          |
| 20PTxxAI             | 20PTxxAI | TO-220AB (insulated)       | 2.3g   | 50        | Tube          |
| 20PTxxH              | 20PTxxH  | TO-263(D <sup>2</sup> PAK) | 2.0g   | 50        | Tube          |

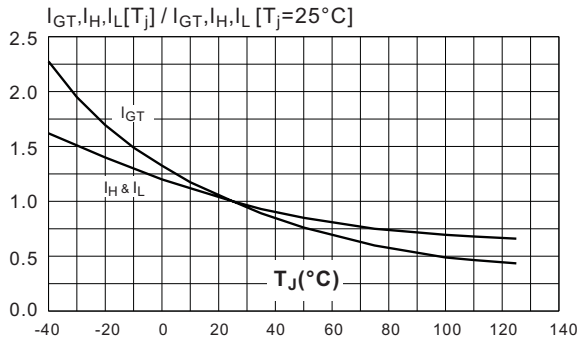
Note: xx = voltage

**ORDERING INFORMATION SCHEME**

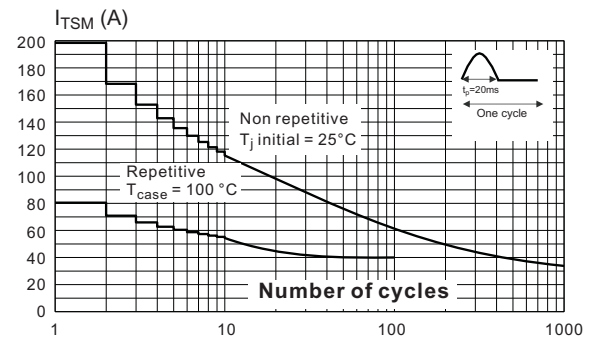
|                                 |           |           |           |           |
|---------------------------------|-----------|-----------|-----------|-----------|
|                                 | <b>20</b> | <b>PT</b> | <b>06</b> | <b>AI</b> |
| <b>Current</b>                  |           |           |           |           |
| 20 = 20A, $I_{T(RMS)}$          |           |           |           |           |
| <b>SCR series</b>               |           |           |           |           |
| <b>Voltage Code</b>             |           |           |           |           |
| 06 = 600V                       |           |           |           |           |
| 08 = 800V                       |           |           |           |           |
| 10 = 1000V                      |           |           |           |           |
| <b>Package type</b>             |           |           |           |           |
| A = TO-220AB (non-insulated)    |           |           |           |           |
| AI = TO-220AB (insulated)       |           |           |           |           |
| H = TO-263 (D <sup>2</sup> PAK) |           |           |           |           |

**Fig.1 Maximum average power dissipation versus average on-state current.**

**Fig.2 Average and D.C. on-state current versus case temperature.**

**Fig.3 Average and D.C. on-state current versus ambient temperature. (copper surface under tab:  $S=1\text{cm}^2$ ) (D<sup>2</sup>PAK)**

**Fig.4 Relative variation of thermal impedance versus pulse duration.**


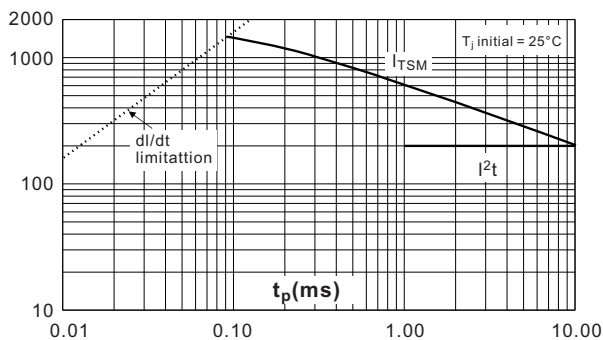
**Fig.5 Relative variation of gate trigger current, holding current and latching current versus junction temperature.**



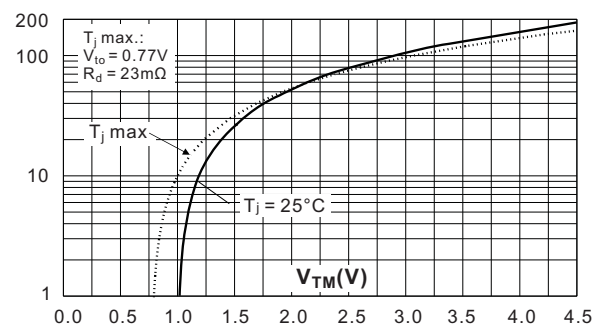
**Fig.6 Surge peak on-state current versus number of cycles.**



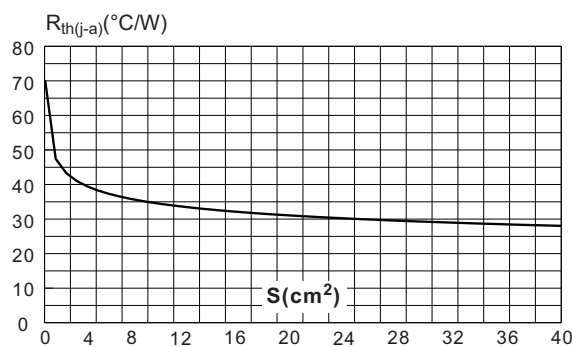
**Fig.7 Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ ms}$ , and corresponding values of  $I^2t$**



**Fig.8 On-state characteristics (maximum values)**

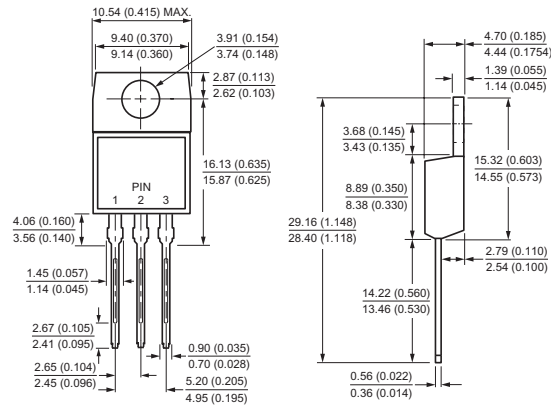


**Fig.9 Thermal resistance junction to ambient versus copper surface under tab (epoxy printed circuit board Fr4, copper thickness: 35  $\mu\text{m}$ )(D<sup>2</sup>PAK)**

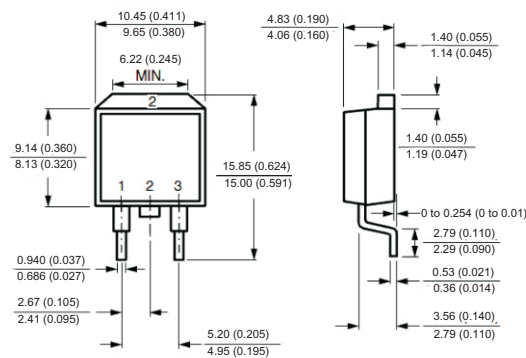


## Case Style

**TO-220AB**



**TO-263(D<sup>2</sup>PAK)**



All dimensions in millimeters(inches)

